

Tezen, Yuta	Aichi	JP
Hiramatsu, Toshio	Aichi	JP

US-CL-CURRENT: 117/103; 117/84, 257/E21.127, 257/E21.131

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KMC](#) | [Drawn D](#)

3. Document ID: US 20040016396 A1

L7: Entry 3 of 34

File: PGPB

Jan 29, 2004

PGPUB-DOCUMENT-NUMBER: 20040016396
 PGPUB-FILING-TYPE: new
 DOCUMENT-IDENTIFIER: US 20040016396 A1

1610 16J396
1610

TITLE: Method for producing semiconductor crystal

PUBLICATION-DATE: January 29, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
<u>Nagai</u> , Seiji	Nishikasugai-gun		JP	
Kojima, Akira	Nishikasugai-gun		JP	
Tomita, Kazuyoshi	Nagoya-shi		JP	

US-CL-CURRENT: 117/84, 257/E21.113, 257/E21.127, 257/E21.131

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4. Document ID: US 20030134446 A1

L7: Entry 4 of 34

File: PGPB

Jul 17, 2003

PGPUB-DOCUMENT-NUMBER: 20030134446
 PGPUB-FILING-TYPE: new
 DOCUMENT-IDENTIFIER: US 20030134446 A1

TITLE: Production method of III nitride compound semiconductor and III nitride compound semiconductor element

PUBLICATION-DATE: July 17, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koike, Masayoshi	Nishikasugai-gun		JP	
Tezen, Yuta	Nishikasugai-gun		JP	
Yamashita, Hiroshi	Nishikasugai-gun		JP	
<u>Nagai</u> , Seiji	Nishikasugai-gun		JP	
Hiramatsu, Toshio	Nishikasugai-gun		JP	

US-CL-CURRENT: 438/41; 257/E21.131

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5. Document ID: US 20030124789 A1

L7: Entry 5 of 34

File: PGPB

Jul 3, 2003

PGPUB-DOCUMENT-NUMBER: 20030124789
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20030124789 A1

TITLE: Semiconductor light-emitting device and manufacturing method thereof

PUBLICATION-DATE: July 3, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koide, Norikatsu	Aichi		JP	
Asami, Shinya	Aichi		JP	
Umezaki, Junichi	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Yamasaki, Shiro	Aichi		JP	
<u>Nagai, Seiji</u>	Aichi		JP	

US-CL-CURRENT: 438/200; 257/E29.078, 257/E33.008, 257/E33.028

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6. Document ID: US 20030010281 A1

L7: Entry 6 of 34

File: PGPB

Jan 16, 2003

PGPUB-DOCUMENT-NUMBER: 20030010281
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20030010281 A1

 TITLE: Semiconductor substrate

PUBLICATION-DATE: January 16, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koike, Masayoshi	Nishikasugai-gun		JP	
<u>Nagai, Seiji</u>	Nishikasugai-gun		JP	

US-CL-CURRENT: 117/97

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KMC](#) | [Drawn D](#)

7. Document ID: US 20020179005 A1

L7: Entry 7 of 34

File: PGPB

Dec 5, 2002

PGPUB-DOCUMENT-NUMBER: 20020179005
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20020179005 A1

~~10/10/02~~ 10/10/02

TITLE: Method for manufacturing group III nitride compound semiconductor and a light-emitting device using group III nitride compound semiconductor

PUBLICATION-DATE: December 5, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koike, Masayoshi	Aichi-ken		JP	
<u>Nagai, Seiji</u>	Aichi-ken		JP	

US-CL-CURRENT: 117/84; 257/E21.113, 257/E21.125

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KAC](#) | [Drawn](#)

 8. Document ID: US 20020146854 A1

L7: Entry 8 of 34

File: PGPB

Oct 10, 2002

PGPUB-DOCUMENT-NUMBER: 20020146854
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20020146854 A1

TITLE: Semiconductor light-emitting device and manufacturing method thereof

PUBLICATION-DATE: October 10, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koide, Norikatsu	Aichi		JP	
Asami, Shinya	Aichi		JP	
Umezaki, Junichi	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Yamasaki, Shiro	Aichi		JP	
<u>Nagai, Seiji</u>	Aichi		JP	

US-CL-CURRENT: 438/22; 257/E29.078, 257/E33.008, 257/E33.028

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KAC](#) | [Drawn](#)

 9. Document ID: US 20020006726 A1

L7: Entry 9 of 34

File: PGPB

Jan 17, 2002

PGPUB-DOCUMENT-NUMBER: 20020006726
 PGPUB-FILING-TYPE: new
 DOCUMENT-IDENTIFIER: US 20020006726 A1

TITLE: METHOD FOR MANUFACTURING GROUP III NITRIDE COMPOUND SEMICONDUCTOR LASER DIODES

PUBLICATION-DATE: January 17, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
YAMASAKI, SHIRO	INAZAWA-SHI		JP	
<u>NAGAI,</u> SEIJI	NAGOYA-SHI		JP	
KOIKE, MASAYOSHI	ICHINOMIYA-SHI		JP	
AKASAKI, ISAMU	NAGOYA-SHI		JP	
AMANO, HIROSHI	NAGOYA-SHI		JP	
YAMADA, ISAO	HIMEJI-SHI		JP	
MASUO, JIRO	KYOTO-SHI		JP	

US-CL-CURRENT: 438/689

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [Claims](#) | [KMC](#) | [Drawn D](#)

10. Document ID: US 20010048112 A1

L7: Entry 10 of 34

File: PGPB

Dec 6, 2001

PGPUB-DOCUMENT-NUMBER: 20010048112
 PGPUB-FILING-TYPE: new
 DOCUMENT-IDENTIFIER: US 20010048112 A1

TITLE: Semiconductor light-emitting device and manufacturing method thereof

PUBLICATION-DATE: December 6, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koide, Norikatsu	Aichi		JP	
Asami, Shinya	Aichi		JP	
Umezaki, Junichi	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Yamasaki, Shiro	Aichi		JP	
<u>Nagai,</u> Seiji	Aichi		JP	

US-CL-CURRENT: 257/94; 257/104, 257/E29.078, 257/E33.008, 257/E33.028

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Terms	Documents
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1. Document ID: US 20040219702 A1

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L7: Entry 1 of 34

File: PGPB

Nov 4, 2004

PGPUB-DOCUMENT-NUMBER: 20040219702

10/2004
762

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040219702 A1

TITLE: Method for manufacturing group-III nitride compound semiconductor, and group-III nitride compound semiconductor device

PUBLICATION-DATE: November 4, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Nagai, Seiji	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Tomita, Kazuyoshi	Aichi		JP	

US-CL-CURRENT: 438/46; 438/47, 438/478, 438/481

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KOMC	Drawn D
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2. Document ID: US 20040123796 A1

L7: Entry 2 of 34

File: PGPB

Jul 1, 2004

PGPUB-DOCUMENT-NUMBER: 20040123796

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040123796 A1

TITLE: Production method for semiconductor crystal and semiconductor luminous element

PUBLICATION-DATE: July 1, 2004

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Nagai, Seiji	Aichi		JP	
Tomita, Kazuyoshi	Aichi		JP	
Yamazaki, Shiro	Aichi		JP	